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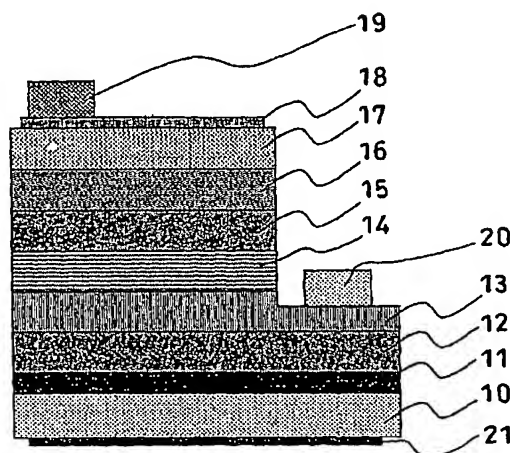
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[Continued on next page]

(54) Title: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE



(57) Abstract: A gallium nitride compound semiconductor light-emitting device includes a crystalline substrate (10), a light-emitting layer (15) of a quantum well structure which is formed of a gallium nitride compound semiconductor barrier layer and a gallium nitride compound semiconductor well layer, which light-emitting layer is provided on a second side of the crystalline substrate, a contact layer (17) formed of a Group III-V compound semiconductor for providing an Ohmic electrode for supplying device operation current to the light-emitting layer, and an Ohmic electrode (18) which is provided on the contact layer and has an aperture through which a portion of the contact layer is exposed. The Ohmic electrode exhibits light permeability with respect to light emitted from the light-emitting layer. The well layer contains a thick portion having a large thickness and a thin portion having a small thickness.



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